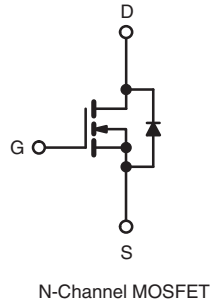


D Series Power MOSFET



RoHS
COMPLIANT
HALOGEN
FREE
Available

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.340
Q_g (Max.) (nC)	90	
Q_{gs} (nC)	14	
Q_{gd} (nC)	22	
Configuration	Single	



FEATURES

- Optimal Design
 - Low Area Specific On-Resistance
 - Low Input Capacitance (C_{iss})
 - Reduced Capacitive Switching Losses
 - High Body Diode Ruggedness
 - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
 - Low Cost
 - Simple Gate Drive Circuitry
 - Low Figure-of-Merit (FOM): $R_{on} \times Q_g$
 - Fast Switching
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Consumer Electronics
 - Displays (LCD or Plasma TV)
- Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
- SMPS

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	SiHP17N60D-E3
Lead (Pb)-free and Halogen-free	SiHP17N60D-GE3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	V_{DS}		600	V
Gate-Source Voltage	V_{GS}		± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	17	A
		$T_C = 100$ °C	10.7	
Pulsed Drain Current ^a	I_{DM}		48	
Linear Derating Factor			2.22	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}		165.6	mJ
Maximum Power Dissipation	P_D		277.8	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	$T_J = 125$ °C		24	V/ns
Reverse Diode dV/dt^d			0.2	
Soldering Recommendations (Peak Temperature) ^c	for 10 s		300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 12$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C.



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.7	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	-	5	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	-	0.275	0.340	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 8\text{ A}$	-	6.2	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$	-	1780	-	μF
Output Capacitance	C_{oss}		-	140	-	
Reverse Transfer Capacitance	C_{rss}		-	15	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V},$ $I_D = 8\text{ A}, V_{DS} = 480\text{ V}$	-	45	90	nC
Gate-Source Charge	Q_{gs}		-	14	-	
Gate-Drain Charge	Q_{gd}		-	22	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}, I_D = 8\text{ A}$ $R_g = 9.1\text{ }\Omega, V_{GS} = 10\text{ V}$	-	22	45	ns
Rise Time	t_r		-	56	85	
Turn-Off Delay Time	$t_{d(off)}$		-	37	75	
Fall Time	t_f		-	30	60	
Internal Gate Resistance	R_g		$f = 1\text{ MHz}, \text{open drain}$	-	1.6	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	17	A
Pulsed Diode Forward Current	I_{SM}		-	-	48	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S,$ $dI/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$	-	633	950	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	7	15	μC
Reverse Recovery Current	I_{RRM}		-	21	42	A

Note

a. Repetitive rating; pulse width limited by maximum junction temperature.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

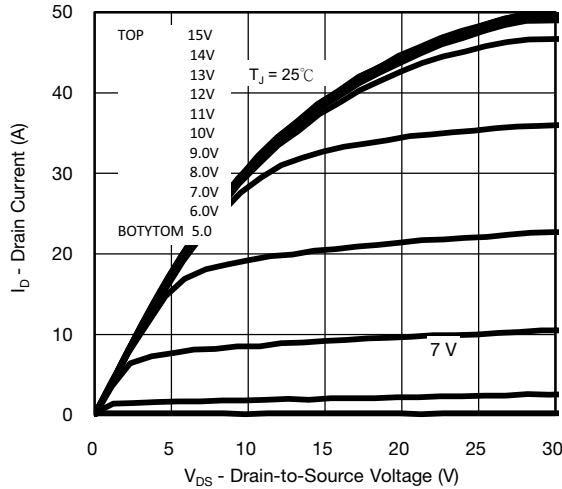


Fig. 1 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

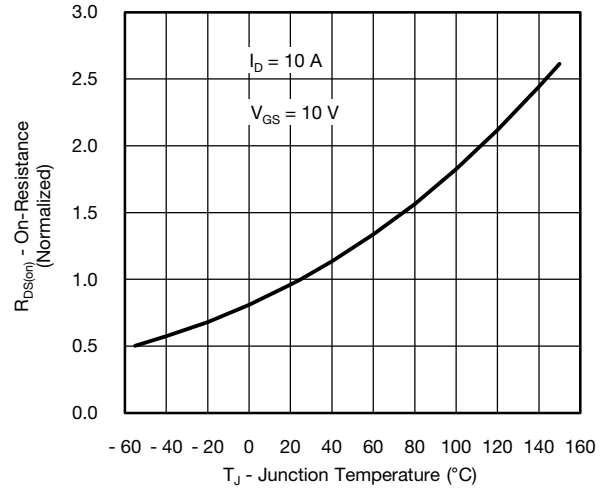


Fig. 4 - Normalized On-Resistance vs. Temperature

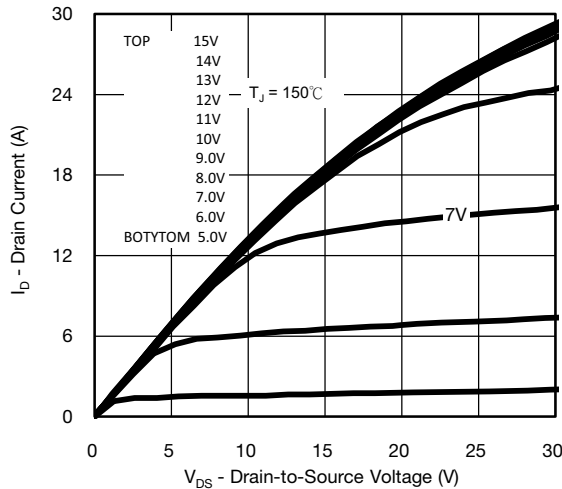


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

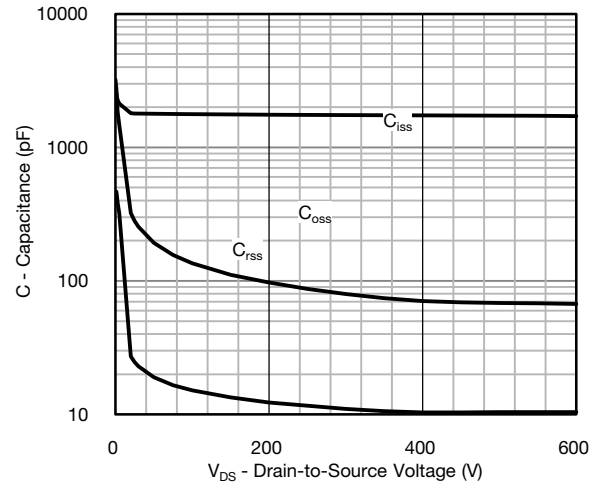


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

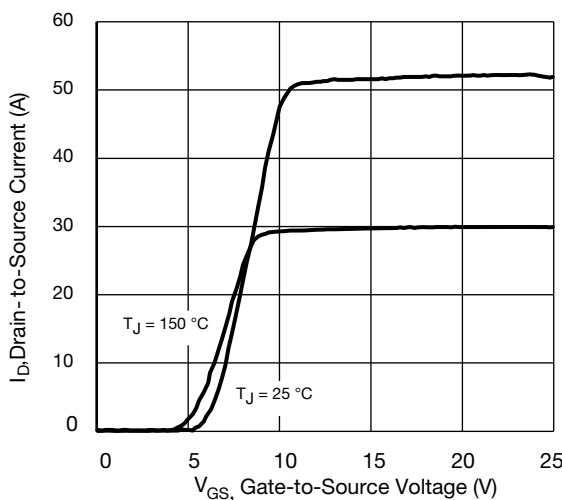


Fig. 3 - Typical Transfer Characteristics

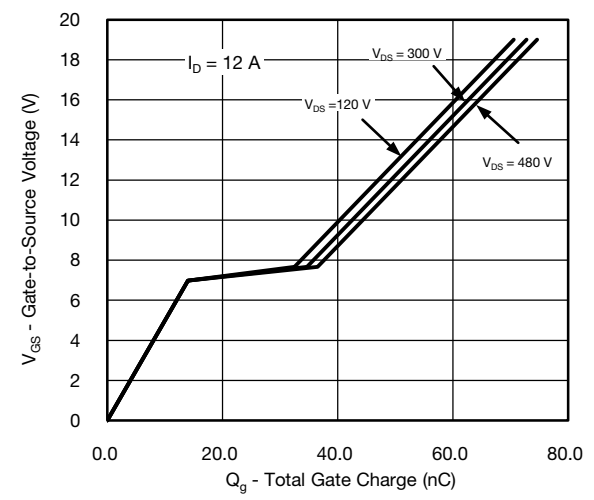


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

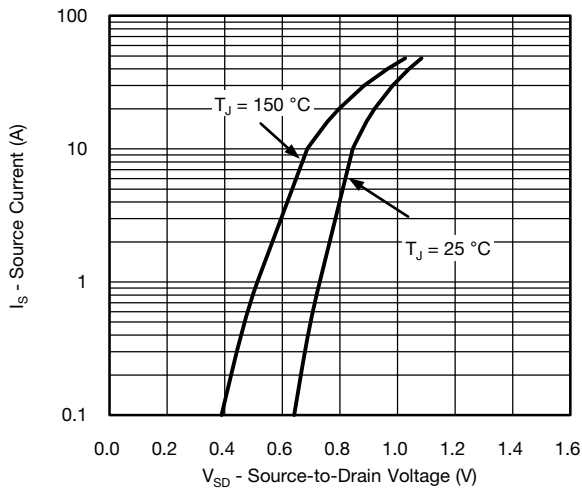


Fig. 7 - Typical Source-Drain Diode Forward Voltage

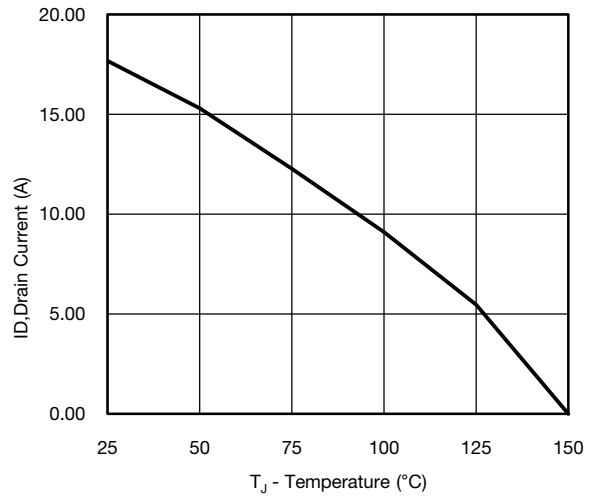


Fig. 9 - Maximum Drain Current vs. Case Temperature

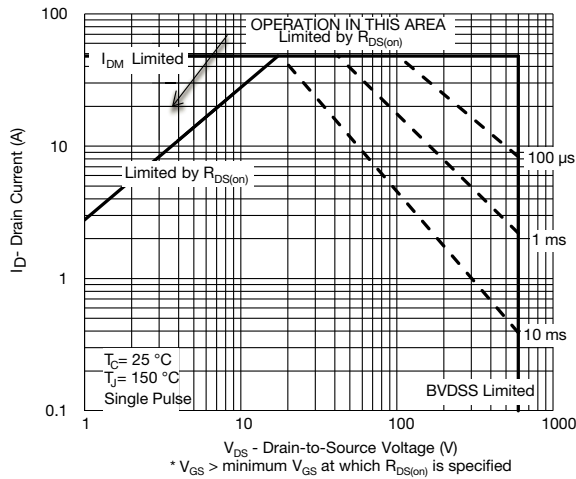


Fig. 8 - Maximum Safe Operating Area

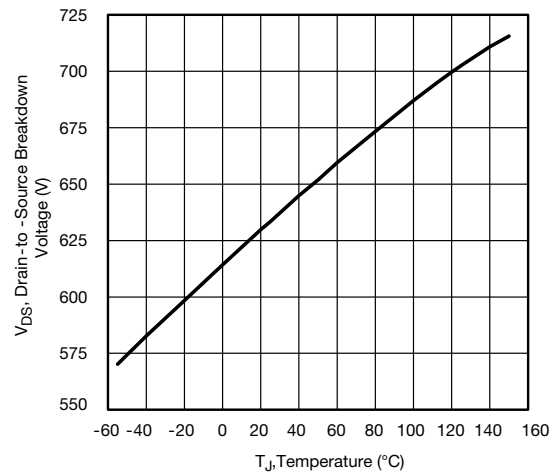


Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

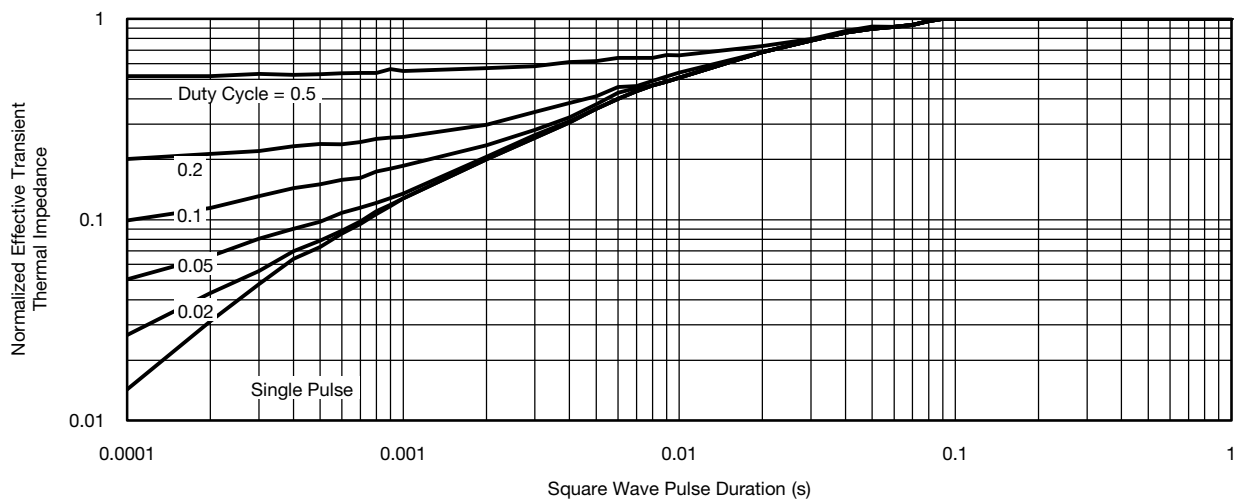


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

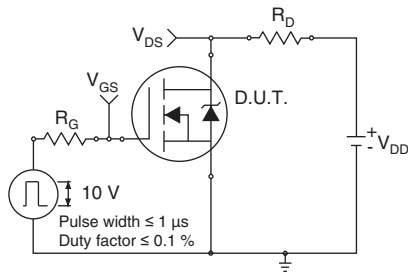


Fig. 12 - Switching Time Test Circuit

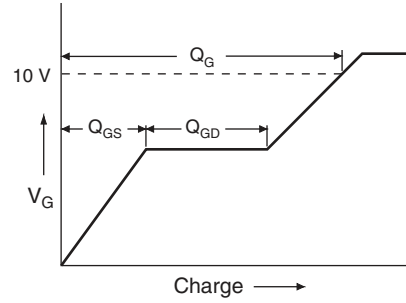


Fig. 16 - Basic Gate Charge Waveform

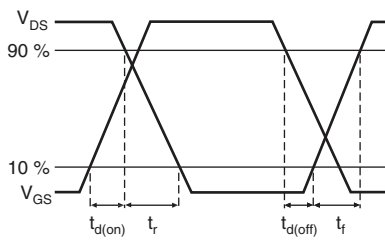


Fig. 13 - Switching Time Waveforms

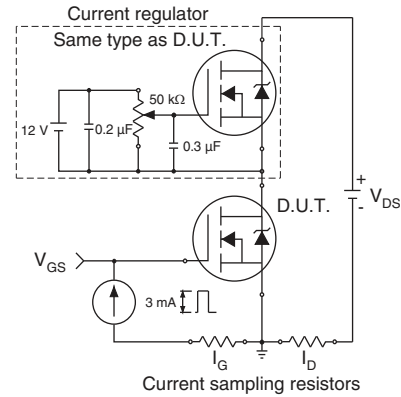


Fig. 17 - Gate Charge Test Circuit

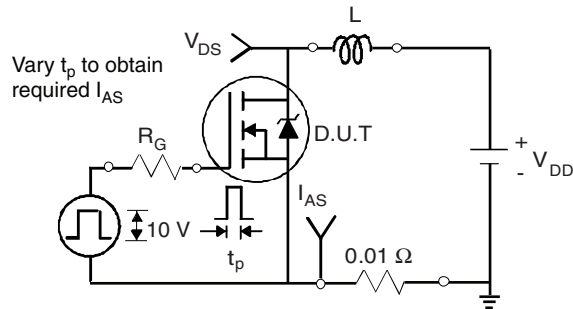


Fig. 14 - Unclamped Inductive Test Circuit

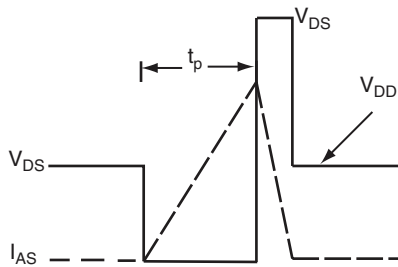
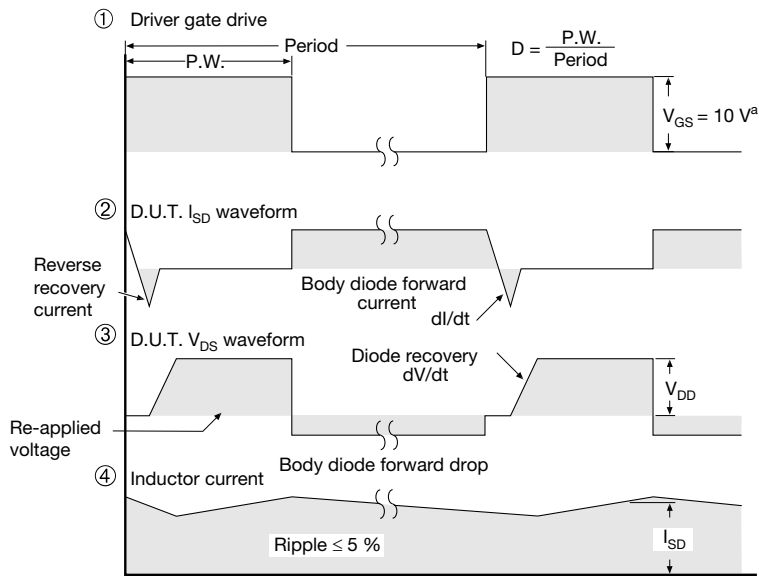
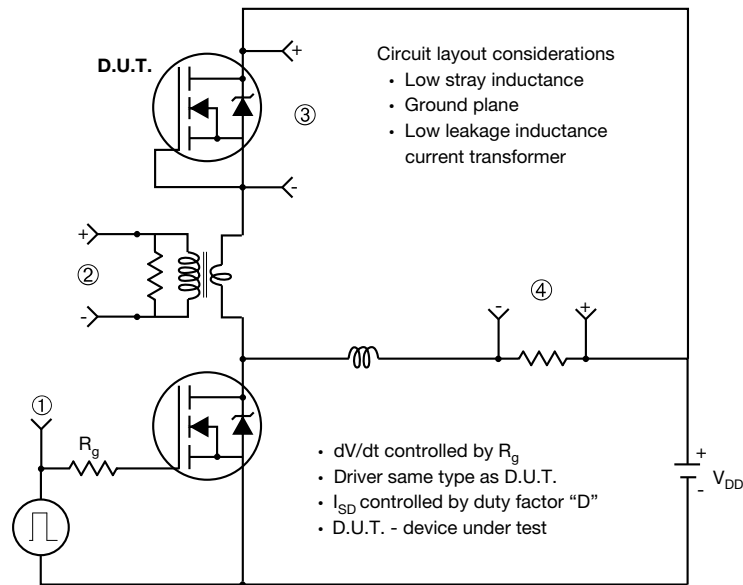


Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-220-1

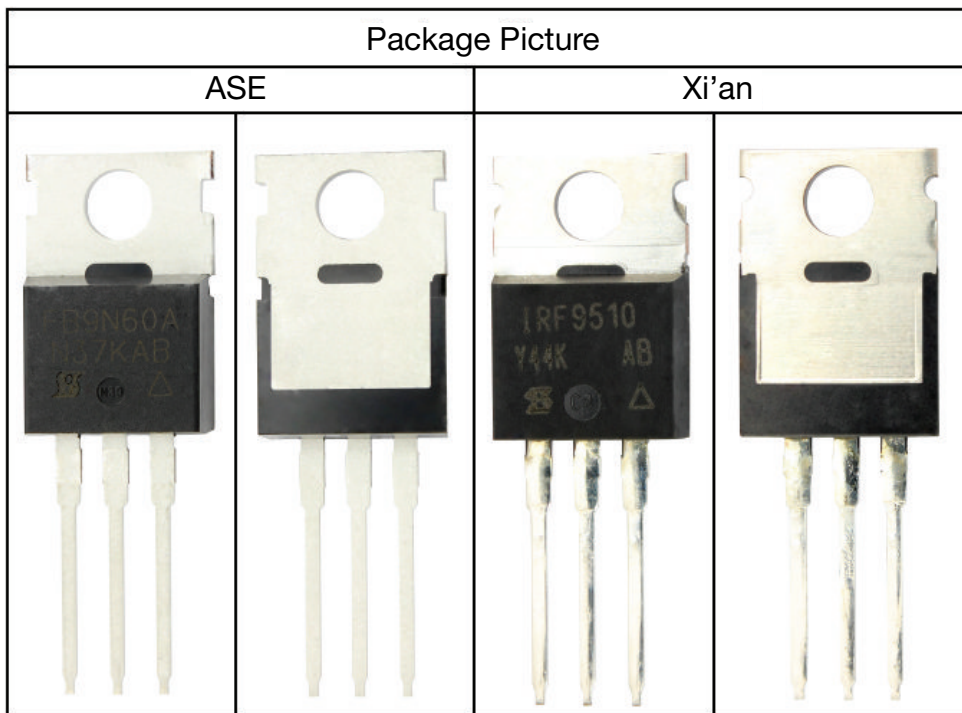


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M^* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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